



浩畅半导体  
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**RB491D** Schottky Barrier Diode

**SOT-23 Plastic-Encapsulate Diodes**

产品规格书 承认书

客户确认:				公司签章:
部门	工程部	品保部	采购部	
签名				
日期				



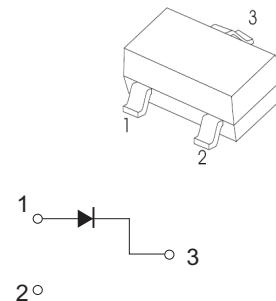
## SOT-23 Plastic-Encapsulated Diodes

### RB491D Schottky Barrier Diode

#### FEATURES

- Small surface mounting type
- Low reverse current and low forward voltage
- High reliability

SOT-23



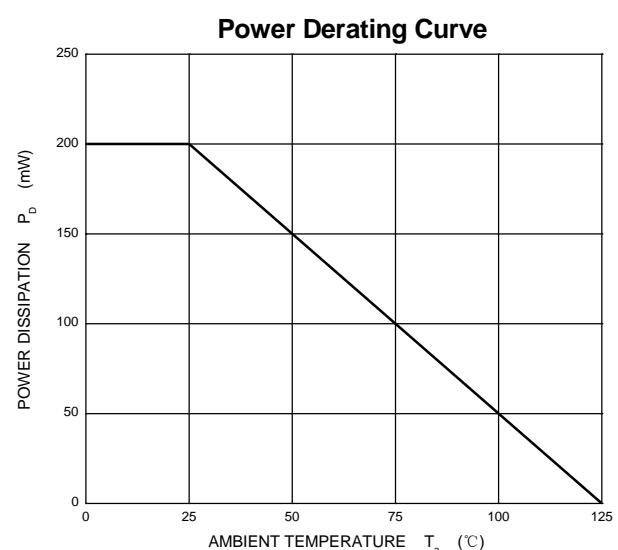
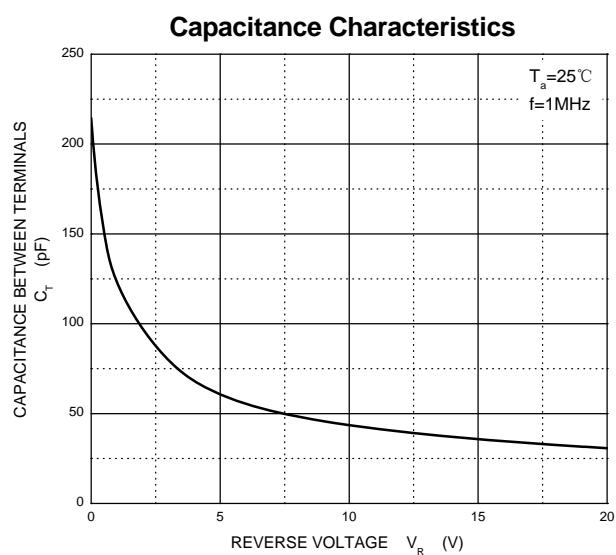
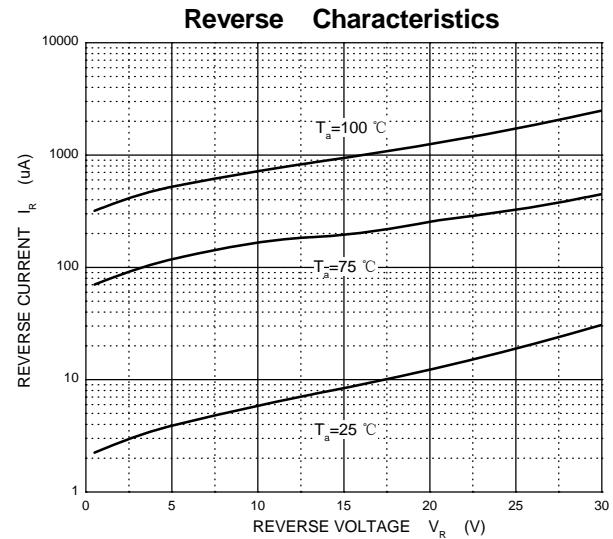
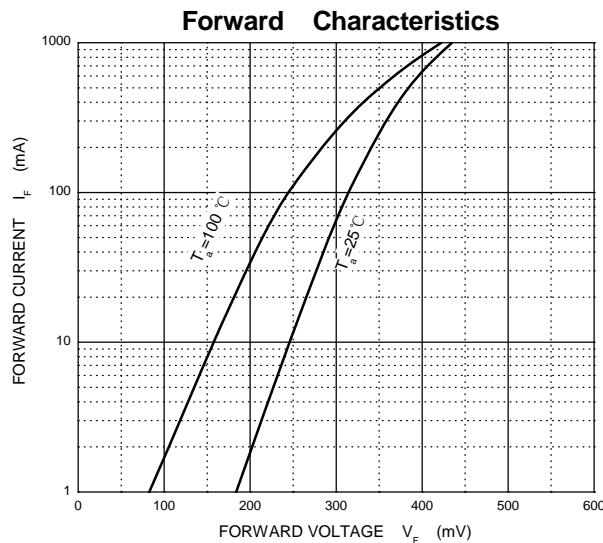
#### Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25°C

Parameter	Symbol	Limit	Unit
Peak reverse voltage	V <sub>RM</sub>	25	V
DC reverse voltage	V <sub>R</sub>	20	V
Mean rectifying current	I <sub>F</sub>	1	A
Non-repetitive Peak Forward Surge Current @t=8.3ms	I <sub>FSM</sub>	3	A
Power dissipation	P <sub>D</sub>	200	mW
Thermal Resistance Junction to Ambient	R <sub>θJA</sub>	500	°C/W
Junction temperature	T <sub>j</sub>	125	°C
Storage temperature	T <sub>stg</sub>	-55~+150	°C

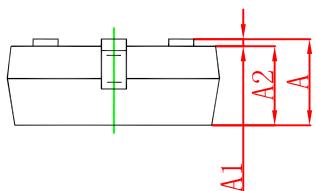
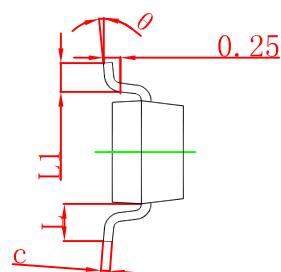
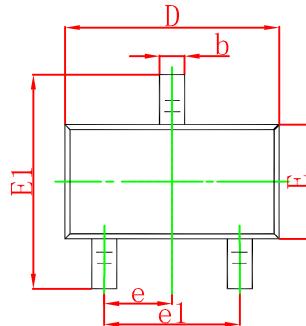
#### Electrical Ratings @Ta=25°C

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Forward voltage	V <sub>F</sub>			0.45	V	I <sub>F</sub> =1A
Reverse current	I <sub>R</sub>			200	μA	V <sub>R</sub> =20V

## Typical Characteristics

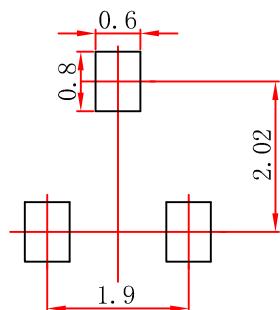


## SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

## SOT-23 Suggested Pad Layout



### Note:

1. Controlling dimension:in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$ .
3. The pad layout is for reference purposes only.